

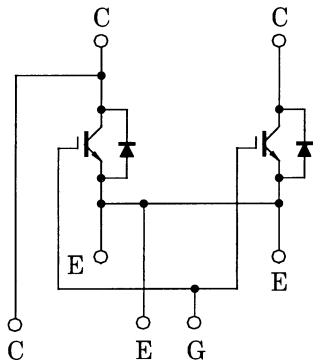
# MG1200V1US51

HIGH POWER SWITCHING APPLICATIONS  
MOTOR CONTROL APPLICATIONS

**FEATURES**

- High Input Impedance
- Enhancement Mode
- Electrodes are isolated from case.

**EQUIVALENT CIRCUIT**



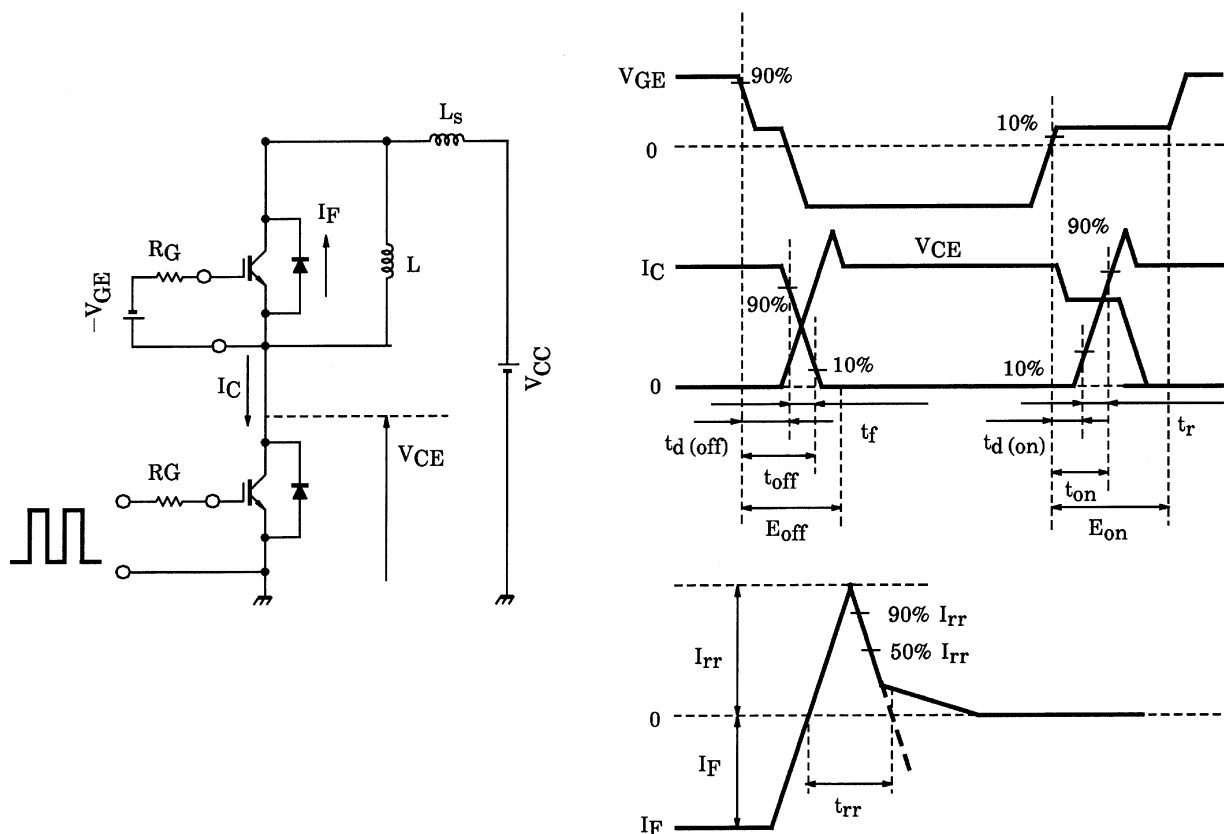
**MAXIMUM RATINGS (Ta = 25°C)**

| CHARACTERISTICS                            |                 | SYMBOL     | RATING            | UNIT |
|--------------------------------------------|-----------------|------------|-------------------|------|
| Collector-Emitter Voltage                  |                 | $V_{CES}$  | 1700              | V    |
| Gate-Emitter Voltage                       |                 | $V_{GES}$  | 20                | V    |
| Collector Current                          | DC              | $I_C$      | 1200              | A    |
|                                            | 1ms             | $I_{CP}$   | 2400              |      |
| Forward Current                            | DC              | $I_F$      | 1200              | A    |
|                                            | 1ms             | $I_{FM}$   | 2400              |      |
| Collector Power Dissipation<br>(Tc = 25°C) |                 | $P_C$      | 5560              | W    |
| Junction Temperature                       |                 | $T_j$      | -20~125           | °C   |
| Storage Temperature Range                  |                 | $T_{stg}$  | -40~125           | °C   |
| Isolation Voltage                          |                 | $V_{Isol}$ | 5400<br>(AC 1min) | V    |
| Screw Torque                               | Terminal: M4/M8 | —          | 2 / 7             | N·m  |
|                                            | Mounting        |            | 4                 |      |

## ELECTRICAL CHARACTERISTICS (Tc = 125°C : except thermal resistance)

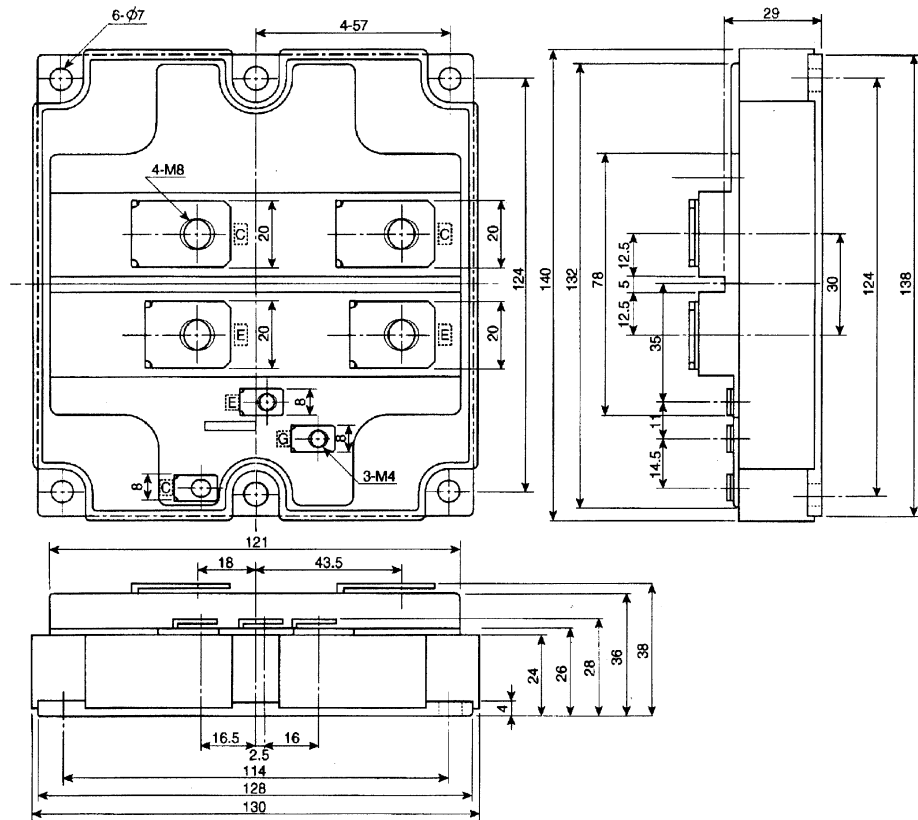
| CHARACTERISTICS                      |               | SYMBOL         | TEST CONDITION                                                                                                                               | MIN | TYP. | MAX      | UNIT                        |
|--------------------------------------|---------------|----------------|----------------------------------------------------------------------------------------------------------------------------------------------|-----|------|----------|-----------------------------|
| Gate Leakage Current                 |               | $I_{GES}$      | $V_{GE} = \pm 20 \text{ V}, V_{CE} = 0 \text{ V}$                                                                                            | —   | —    | $\pm 50$ | nA                          |
| Collector Cut-Off Current            |               | $I_{CES}$      | $V_{CE} = 1700 \text{ V}, V_{GE} = 0 \text{ V}$                                                                                              | —   | —    | 100      | mA                          |
| Gate-Emitter Cut-Off Voltage         |               | $V_{GE (off)}$ | $V_{CE} = 5 \text{ V}, I_C = 1.2 \text{ A}$                                                                                                  | 3.0 | —    | 7.0      | V                           |
| Collector-Emitter Saturation Voltage |               | $V_{CE (sat)}$ | $V_{GE} = 15 \text{ V}, I_C = 1200 \text{ A}$                                                                                                | —   | —    | 5.0      | V                           |
| Input Capacitance                    |               | $C_{ies}$      | $V_{CE} = 10 \text{ V}, V_{GE} = 0 \text{ V}, f = 300 \text{ kHz}$                                                                           | —   | 130  | —        | nF                          |
| Switching Time<br>(Note 1)           | Rise Time     | $t_r$          | $V_{CC} = 900 \text{ V}, I_C = 1200 \text{ A}$<br>$V_{GE} = \pm 15 \text{ V}, R_G = 1.8 \Omega$<br>(Inductive load: $L_s = 150 \text{ nH}$ ) | —   | —    | 0.7      | $\mu\text{s}$               |
|                                      | Turn-On Time  | $t_{on}$       |                                                                                                                                              | —   | —    | 1.0      | $\mu\text{s}$               |
|                                      | Fall Time     | $t_f$          |                                                                                                                                              | —   | —    | 0.8      | $\mu\text{s}$               |
|                                      | Turn-Off Time | $t_{off}$      |                                                                                                                                              | —   | —    | 1.5      | $\mu\text{s}$               |
| Forward Voltage                      |               | $V_F$          | $I_F = 1200 \text{ A}, V_{GE} = 0 \text{ V}$                                                                                                 | —   | —    | 3.2      | V                           |
| Reverse Recovery Time<br>(Note 1)    |               | $t_{rr}$       | $I_F = 1200 \text{ A}, V_{GE} = 15 \text{ V}$<br>$di/dt = 4000 \text{ A}/\mu\text{s}, V_{CC} = 900 \text{ V}$                                | —   | —    | 0.8      | $\mu\text{s}$               |
| Switching Dissipation<br>(Note 1)    | Turn-On Loss  | $E_{on}$       | $V_{CC} = 900 \text{ V}, I_C = 1200 \text{ A}$<br>$V_{GE} = \pm 15 \text{ V}, R_G = 1.8 \Omega$                                              | —   | 250  | —        | mJ                          |
|                                      | Turn-Off Loss | $E_{off}$      | $V_{CC} = 900 \text{ V}, I_C = 1200 \text{ A}$<br>$V_{GE} = \pm 15 \text{ V}, R_G = 1.8 \Omega$                                              | —   | 500  | —        | mJ                          |
|                                      | Diode Loss    | $E_{dsw}$      | $I_F = 1200 \text{ A}, V_{GE} = -15 \text{ V}$<br>$di/dt = 4000 \text{ A}/\mu\text{s}, V_{CC} = 900 \text{ V}$                               | —   | 300  | —        | mJ                          |
| Thermal Resistance                   |               | $R_{th (j-c)}$ | Transistor (IGBT) Stage<br>Diode Stage                                                                                                       | —   | —    | 0.018    | $^{\circ}\text{C}/\text{W}$ |
|                                      |               |                |                                                                                                                                              | —   | —    | 0.035    | $^{\circ}\text{C}/\text{W}$ |

Note 1: Test circuit and timing chart of switching time, reverse recovery time and switching dissipation.



## PACKAGE DIMENSIONS: TOSHIBA 2-142A1A

Unit: mm



Weight: 900 g (typ.)

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